

Thyristor \ Diode Module

$$V_{RRM} = 2 \times 1600 \text{ V}$$

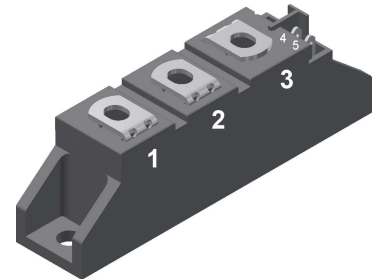
$$I_{TAV} = 116 \text{ A}$$

$$V_T = 1.28 \text{ V}$$

Phase leg

Part number

MCD95-16io1



Backside: isolated

 E72873



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al₂O₃-ceramic

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: TO-240AA

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

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Rectifier			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1700	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1600	V
I_{RD}	reverse current, drain current	$V_{R/D} = 1600 V$	$T_{VJ} = 25^{\circ}C$		200	μA
		$V_{R/D} = 1600 V$	$T_{VJ} = 125^{\circ}C$		5	mA
V_T	forward voltage drop	$I_T = 150 A$	$T_{VJ} = 25^{\circ}C$		1.29	V
		$I_T = 300 A$			1.50	V
		$I_T = 150 A$	$T_{VJ} = 125^{\circ}C$		1.28	V
		$I_T = 300 A$			1.70	V
I_{TAV}	average forward current	$T_C = 85^{\circ}C$	$T_{VJ} = 125^{\circ}C$		116	A
$I_{T(RMS)}$	RMS forward current	180° sine			182	A
V_{T0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 125^{\circ}C$		0.85	V
r_T	slope resistance				2.4	m Ω
R_{thJC}	thermal resistance junction to case				0.22	K/W
R_{thCH}	thermal resistance case to heatsink			0.2		K/W
P_{tot}	total power dissipation		$T_C = 25^{\circ}C$		455	W
I_{TSM}	max. forward surge current	$t = 10 ms; (50 Hz), sine$	$T_{VJ} = 45^{\circ}C$		2.25	kA
		$t = 8,3 ms; (60 Hz), sine$	$V_R = 0 V$		2.43	kA
		$t = 10 ms; (50 Hz), sine$	$T_{VJ} = 125^{\circ}C$		1.92	kA
		$t = 8,3 ms; (60 Hz), sine$	$V_R = 0 V$		2.07	kA
I^2t	value for fusing	$t = 10 ms; (50 Hz), sine$	$T_{VJ} = 45^{\circ}C$		25.3	kA ² s
		$t = 8,3 ms; (60 Hz), sine$	$V_R = 0 V$		24.6	kA ² s
		$t = 10 ms; (50 Hz), sine$	$T_{VJ} = 125^{\circ}C$		18.3	kA ² s
		$t = 8,3 ms; (60 Hz), sine$	$V_R = 0 V$		17.7	kA ² s
C_J	junction capacitance	$V_R = 400 V \quad f = 1 MHz$	$T_{VJ} = 25^{\circ}C$		119	pF
P_{GM}	max. gate power dissipation	$t_p = 30 \mu s$	$T_C = 125^{\circ}C$		10	W
		$t_p = 300 \mu s$			5	W
P_{GAV}	average gate power dissipation				0.5	W
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 125^{\circ}C; f = 50 Hz$	repetitive, $I_T = 250 A$		150	A/ μs
		$t_p = 200 \mu s; di_G/dt = 0.45 A/\mu s;$ $I_G = 0.45 A; V = \frac{2}{3} V_{DRM}$	non-repet., $I_T = 116 A$		500	A/ μs
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$ $R_{GK} = \infty; \text{method 1 (linear voltage rise)}$	$T_{VJ} = 125^{\circ}C$		1000	V/ μs
V_{GT}	gate trigger voltage	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		2.5	V
			$T_{VJ} = -40^{\circ}C$		2.6	V
I_{GT}	gate trigger current	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		150	mA
			$T_{VJ} = -40^{\circ}C$		200	mA
V_{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 125^{\circ}C$		0.2	V
I_{GD}	gate non-trigger current				10	mA
I_L	latching current	$t_p = 10 \mu s$	$T_{VJ} = 25^{\circ}C$		450	mA
		$I_G = 0.45 A; di_G/dt = 0.45 A/\mu s$				
I_H	holding current	$V_D = 6 V \quad R_{GK} = \infty$	$T_{VJ} = 25^{\circ}C$		200	mA
t_{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^{\circ}C$		2	μs
		$I_G = 0.45 A; di_G/dt = 0.45 A/\mu s$				
t_q	turn-off time	$V_R = 100 V; I_T = 150 A; V = \frac{2}{3} V_{DRM}$ $di/dt = 10 A/\mu s \quad dv/dt = 20 V/\mu s \quad t_p = 200 \mu s$	$T_{VJ} = 100^{\circ}C$		185	μs



Package TO-240AA				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
I_{RMS}	RMS current	per terminal			200	A	
T_{VJ}	virtual junction temperature		-40		125	°C	
T_{op}	operation temperature		-40		100	°C	
T_{stg}	storage temperature		-40		125	°C	
Weight					81	g	
M_D	mounting torque		2.5		4	Nm	
M_T	terminal torque		2.5		4	Nm	
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	13.0	9.7		mm	
$d_{Spb/Apb}$		terminal to backside	16.0	16.0		mm	
V_{ISOL}	isolation voltage	t = 1 second		4800		V	
		t = 1 minute	50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	4000		V	



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCD95-16IO1	MCD95-16IO1	Box	36	464872

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 125^{\circ}\text{C}$

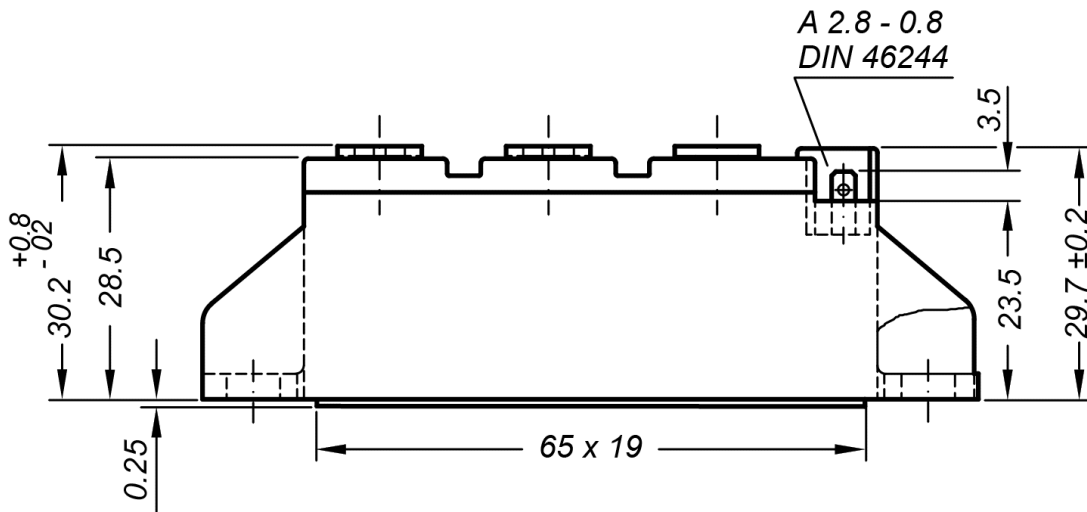


Thyristor

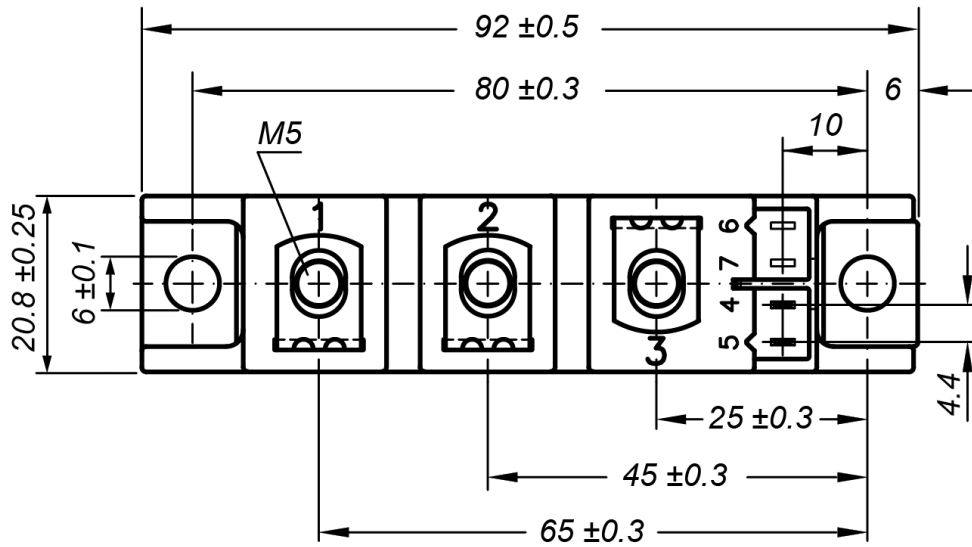
$V_{0\ max}$	threshold voltage	0.85	V
$R_{0\ max}$	slope resistance *	1.2	mΩ



Outlines TO-240AA



General tolerance: DIN ISO 2768 class „c“



Optional accessories for modules

Keyed gate/cathode twin plugs with wire length = 350 mm, gate = white, cathode = red
Type ZY 200L (L = Left for pin pair 4/5) UL 758, style 3751



Thyristor



Fig. 1 Surge overload current I_{TSM} ,
 I_{FSM} : Crest value, t: duration



Fig. 2 I^2t versus time (1-10 ms)



Fig. 3 Max. forward current at case temperature



Fig. 4 Power dissipation vs. on-state current & ambient temperature (per thyristor or diode)

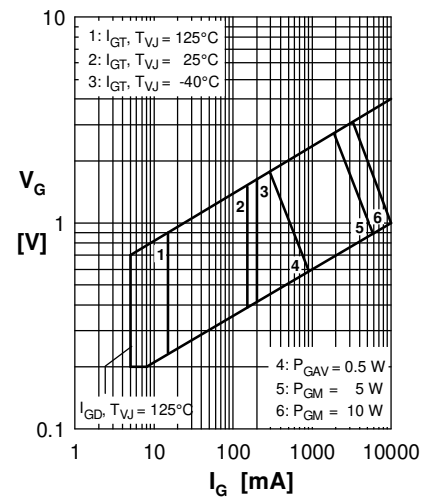


Fig. 5 Gate trigger characteristics



Fig. 6 Three phase rectifier bridge: Power dissipation vs. direct output current and ambient temperature

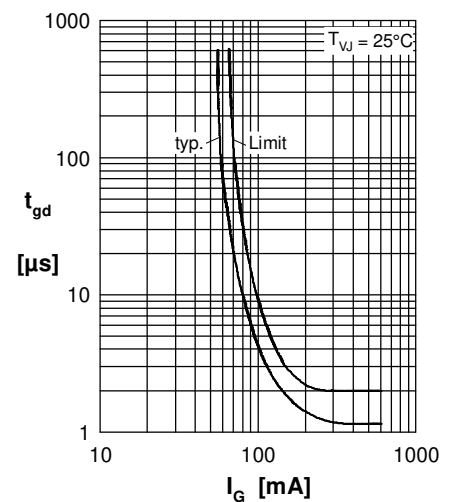


Fig. 7 Gate controlled delay time

Rectifier


Fig. 8 Three phase AC-controller: Power dissipation versus RMS output current and ambient temperature

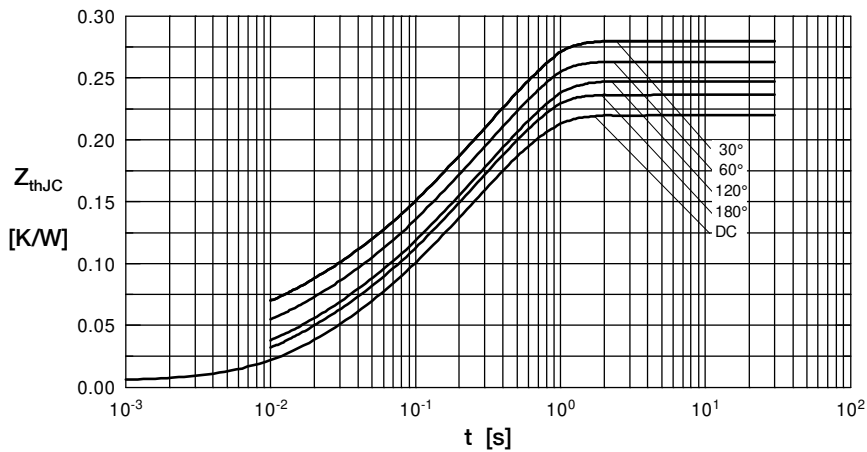


Fig. 9 Transient thermal impedance junction to case (per thyristor/diode)

R_{thJC} for various conduction angles d:

d	R_{thJC} [K/W]
DC	0.22
180°	0.23
120°	0.25
60°	0.27
30°	0.28

Constants for Z_{thJC} calculation:

i	R_{thi} [K/W]	t_i [s]
1	0.0066	0.0019
2	0.0678	0.0477
3	0.1456	0.3440



Fig. 10 Transient thermal impedance junction to heatsink (per thyristor/diode)

R_{thJK} for various conduction angles d:

d	R_{thJK} [K/W]
DC	0.42
180°	0.43
120°	0.45
60°	0.47
30°	0.48

Constants for Z_{thJK} calculation:

i	R_{thi} [K/W]	t_i [s]
1	0.0066	0.0019
2	0.0678	0.0477
3	0.1456	0.3440
4	0.2000	1.3200



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- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

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- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



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